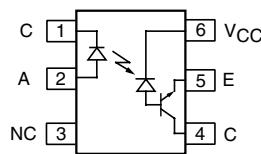
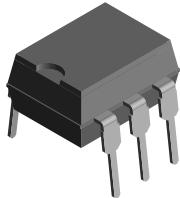


Optocoupler, High Speed Phototransistor Output, 1 Mbd, 10 kV/ms CMR, Split Collector Transistor Output



i179064

DESCRIPTION

The SFH636 is an optocoupler with a GaAlAs infrared emitting diode, optically coupled to an integrated photo detector consisting of a photo diode and a high speed transistor in a DIP-6 plastic package. The device is functionally similar to 6N136 except there is no base connection, and the electrical foot print is different. Noise and dv/dt performance is enhanced by not bringing out the base connection.

Signals can be transmitted between two electrically separated circuits up to frequencies of 2.0 MHz. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference.

FEATURES

- High speed optocoupler without base connection
- Isolation test voltage: 5300 V_{RMS}
- GaAlAs emitter
- Integrated detector with photo diode and transistor
- High data transmission rate: 1.0 MBit/s
- TTL compatible
- Open collector output
- CTR at $I_F = 16 \text{ mA}$, $V_O = 0.4 \text{ V}$, $V_{CC} = 4.5 \text{ V}$, $T_{amb} = 25^\circ\text{C}$: $\geq 19 \%$
- Good CTR linearity relative to forward current
- Low coupling capacitance
- dV/dt : typ. 10 kV/ μs
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



APPLICATIONS

- IGBT drivers
- Data communications
- Programmable controllers

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending available with option 1

ORDER INFORMATION

PART	REMARKS
SFH636	CTR $\geq 19 \%$, DIP-6
SFH636-X006	CTR $\geq 19 \%$, DIP-6 400 mil (option 6)
SFH636-X007	CTR $\geq 19 \%$, SMD-6 (option 7)
SFH636-X009	CTR $\geq 19 \%$, SMD-6 (option 9)

Note

For additional information on the available options refer to option information.

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	3.0	V
DC forward current		I_F	25	mA
Surge forward current	$t_P \leq 1.0 \mu\text{s}$, 300 pulses/s	I_{FSM}	1.0	A
Power dissipation		P_{diss}	45	mW

SFH636



Vishay Semiconductors Optocoupler, High Speed Phototransistor Output,
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ABSOLUTE MAXIMUM RATINGS ⁽¹⁾

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
OUTPUT				
Supply voltage		V_S	- 0.5 to 30	V
Output voltage		V_O	- 0.5 to 20	V
Output current		I_O	8.0	mA
Power dissipation		P_{diss}	100	mW
COUPLER				
Isolation test voltage between emitter and detector, refer to climate DIN 40046, part 2, Nov. 74		V_{ISO}	5300	V_{RMS}
Creepage distance			≥ 7	mm
Clearance distance			≥ 7	mm
Isolation resistance	$V_{IO} = 500 \text{ V}, T_{amb} = 25 \text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{12}$	Ω
	$V_{IO} = 500 \text{ V}, T_{amb} = 100 \text{ }^{\circ}\text{C}$	R_{IO}	$\geq 10^{11}$	Ω
Storage temperature range		T_{stg}	- 55 to + 150	$^{\circ}\text{C}$
Ambient temperature range		T_{amb}	- 55 to +100	$^{\circ}\text{C}$
Junction temperature		T_j	100	$^{\circ}\text{C}$
Soldering temperature ⁽²⁾	max. 10 s, dip soldering: distance to seating plane $\geq 1.5 \text{ mm}$	T_{sld}	260	$^{\circ}\text{C}$

Notes

(1) $T_{amb} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

(2) Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS

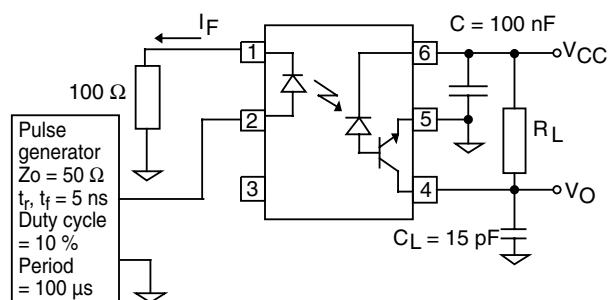
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 16 \text{ mA}$	V_F		1.5	1.8	V
Reverse current	$V_R = 3.0 \text{ V}$	I_R		0.5	10	μA
Capacitance	$V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$	C_O		125		pF
Thermal resistance		R_{thja}		700		K/W
OUTPUT						
Logic high supply current	$I_F = 0 \text{ V}, V_O \text{ (open)}, V_{CC} = 15 \text{ V}$	I_{CCH}		0.01	1.0	μA
	$I_F = 0 \text{ V}, V_O \text{ (open)}, V_{CC} = 15 \text{ V}$	I_{CCH}		0.01	2.0	μA
Output current, output high	$I_F = 0 \text{ V}, V_O \text{ (open)}, V_{CC} = 5.5 \text{ V}$	I_{OH}		0.003	0.5	μA
	$I_F = 0 \text{ V}, V_O \text{ (open)}, V_{CC} = 15 \text{ V}$	I_{OH}		0.01	1.0	μA
	$I_F = 0 \text{ V}, V_O \text{ (open)}, V_{CC} = 15 \text{ V}$	I_{OH}			50	μA
Collector emitter capacitance	$V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$	C_{CE}		3.0		pF
Thermal resistance		R_{thja}		300		K/W
COUPLER						
Coupling capacitance		C_c		0.6		pF
Collector emitter saturation voltage	$I_F = 16 \text{ mA}, I_O = 2.4 \text{ mA}, V_{CC} = 4.5 \text{ V}$	V_{OL}		0.1	0.4	V
Supply current, logic low	$I_F = 16 \text{ mA}, V_O \text{ open}, V_{CC} = 15 \text{ V}$	I_{DD}		80		

Note

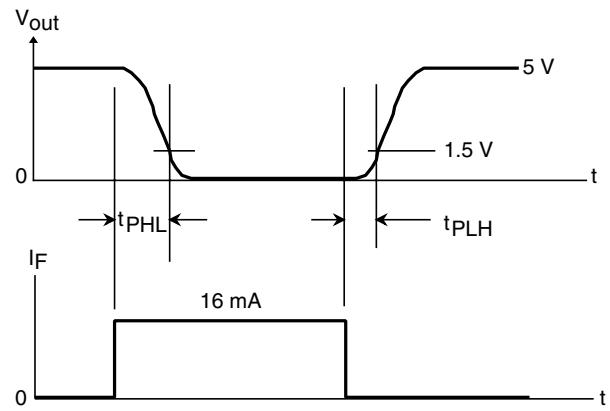
$T_{amb} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

**Optocoupler, High Speed Phototransistor Output, Vishay Semiconductors
1 Mbd,
10 kV/ms CMR, Split Collector Transistor Output**



isfh636_01



isfh636_02

Fig. 1 - Test Setup

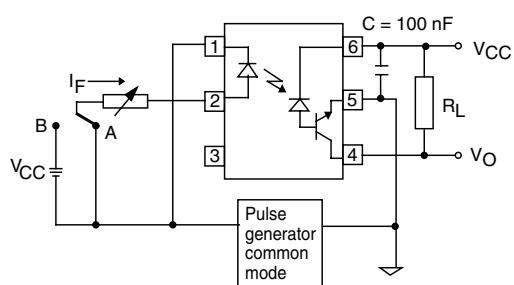
Fig. 2 - Switching Time Measurement

CURRENT TRANSFER RATIO

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_F = 16 mA, V_O = 0.4 V, V_CC = 4.5 V	I_C/I_F	19	30		%
	I_F = 16 mA, V_O = 0.5 V, V_CC = 4.5 V	I_C/I_F	15			%

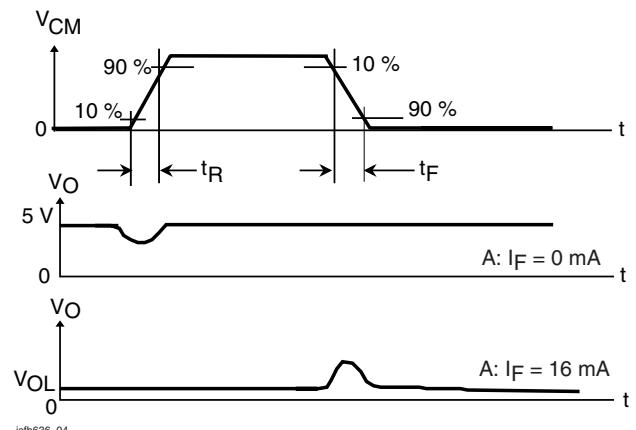
SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Propagation delay time (high to low)	I_F = 16 mA, V_CC = 5.0 V, R_L = 1.9 kΩ	t_PHL		0.3	0.8	μs
Propagation delay time (low to low)	I_F = 16 mA, V_CC = 5.0 V, R_L = 1.9 kΩ	t_PLH		0.3	0.8	μs



isfh636_03

Fig. 3 - Common Mode Transient Test



isfh636_04

Fig. 4 - Measurement Waveform of CMR

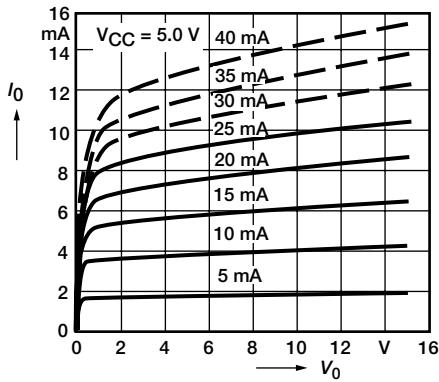
COMMON MODE TRANSIENT IMMUNITY

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Common mode transient immunity (high)	I_O = 0 mA, V_CM = 1500 V_P-P, R_L = 1.9 kΩ, V_CC = 5.0 V	CM_H		10		kV/μs
Common mode transient immunity (low)	I_O = 16 mA, V_CM = 1500 V_P-P, R_L = 1.9 kΩ, V_CC = 5.0 V	CM_L		10		kV/μs

Vishay Semiconductors Optocoupler, High Speed Phototransistor Output,
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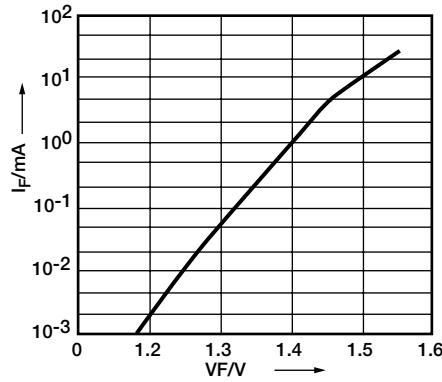
TYPICAL CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



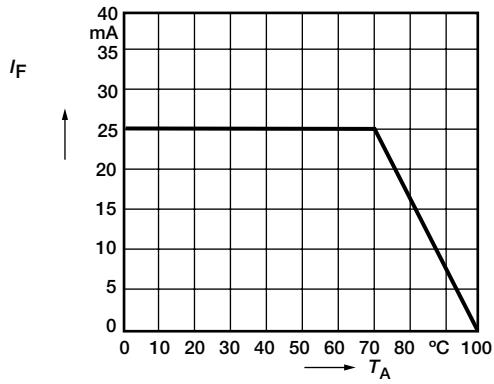
isfh636_05

Fig. 5 - Output Characteristics-Output Current vs. Output Voltage



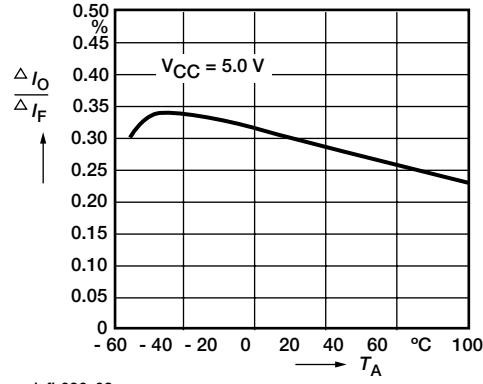
isfh636_08

Fig. 8 - Forward Current of Emitting Diode vs. Forward Voltage



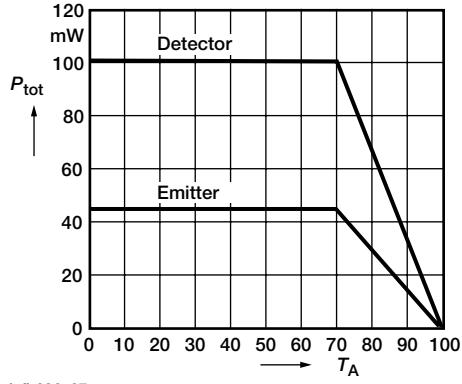
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Fig. 6 - Permissible Forward Current of Emitting Diode vs. Ambient Temperature



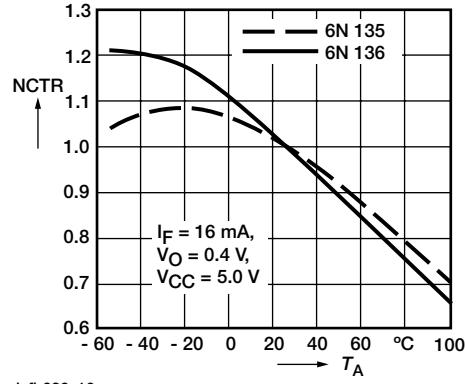
isfh636_09

Fig. 9 - Small Signal Transfer Ratio vs. Forward Current



isfh636_07

Fig. 7 - Permissible Total Power Dissipation vs. Ambient Temperature



isfh636_10

Fig. 10 - Current Transfer Ratio (Normalized) vs. Ambient Temperature

**Optocoupler, High Speed Phototransistor Output, Vishay Semiconductors
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10 kV/ms CMR, Split Collector Transistor Output**

Fig. 12 - Delay Times vs. Ambient Temperature

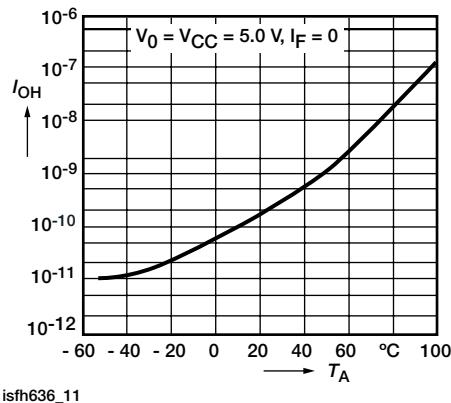


Fig. 11 - Output Current (High) vs. Ambient Temperature

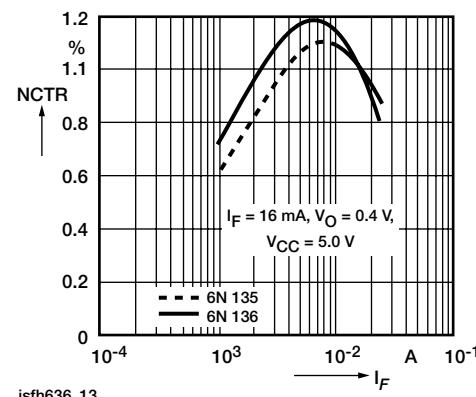
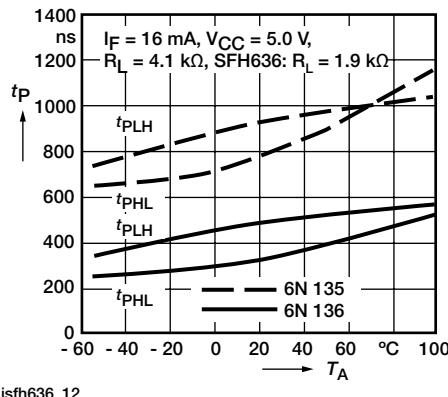
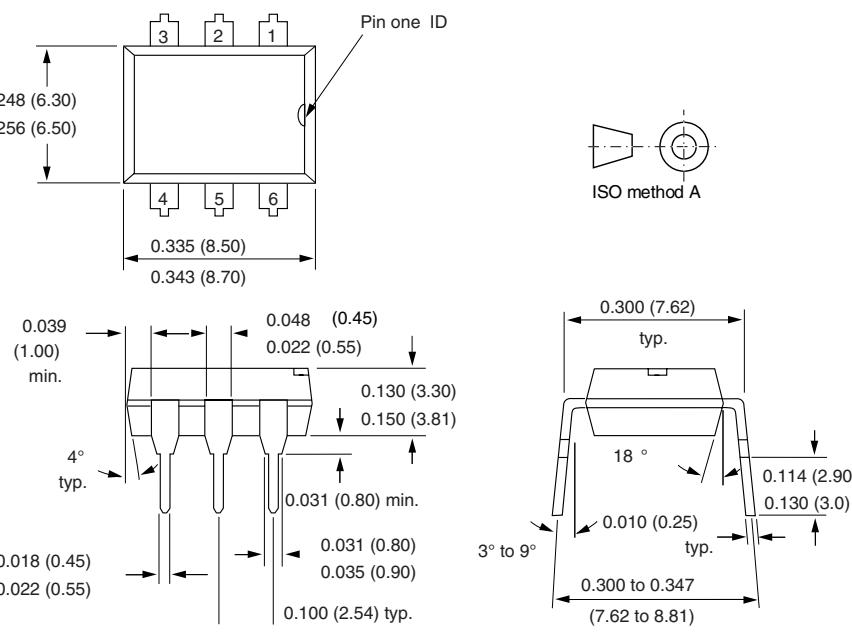


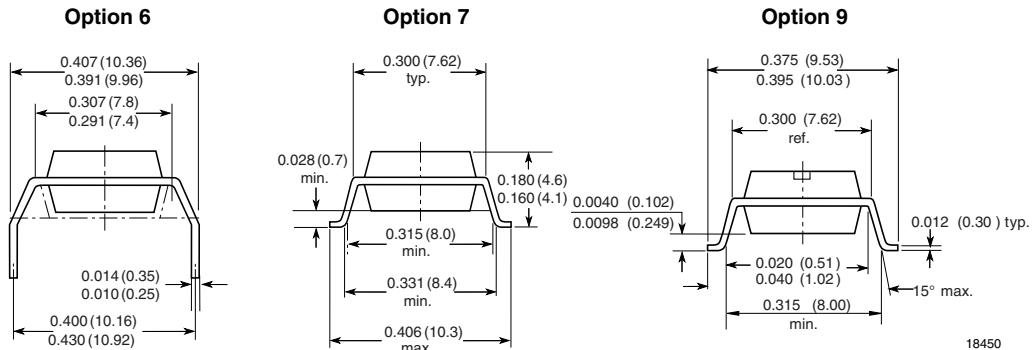
Fig. 13 - Current Transfer Ratio (Normalized) vs. Forward Current



PACKAGE DIMENSIONS in inches (millimeters)



Vishay Semiconductors Optocoupler, High Speed Phototransistor Output,
1 Mbd,
10 kV/ms CMR, Split Collector Transistor Output





Optocoupler, High Speed Phototransistor Output, Vishay Semiconductors
1 Mbd,
10 kV/ms CMR, Split Collector Transistor Output

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It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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